Dkt. 2271/62289-Z

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of:		Seiji SARAYAMA, et al.	
Serial No.	:	Con't of 09/590,063	Group Art Unit: 2811
Date Filed	:	Concurrently Herewith	Examiner:
For	:	PRODUCTION OF A GaN BULK CRYSTAL SUBSTRATE AND A SEMICONDUCTOR DEVICE FORMED ON A GaN BULK CRYSTAL SUBSTRATE	

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Commissioner For Patents
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PRELIMINARY AMENDMENT

Sir:

Prior to examination of the above-identified application, which is a division of application Serial No. 09/590,063, filed June 8, 2000, Applicants respectfully request that the above identified application be amended as follows.

In the Specification

Page 32, delete lines 10-26, and replace with --From the x-ray diffraction peak position data, it was confirmed that the cubic GaN bulk crystal 102B thus formed has a cubic lattice constant a_0 of 4.5063 ± 0.0009Å. Fig. 19 shows x-ray diffraction intensity data obtained for a GaN bulk crystal grown by the apparatus of Fig. 3 as the bulk crystal 102B at a temperature of 750°C under the total pressure of 7MPa in the reaction vessel 101. In Fig. 19, it should be noted that the Fo represents the structural factor obtained from the diffraction intensity data for each of the reflections (h k 1) and s represents the error factor of the measurement, while Fc represents the structural factor calculated from a cubic zinc blende